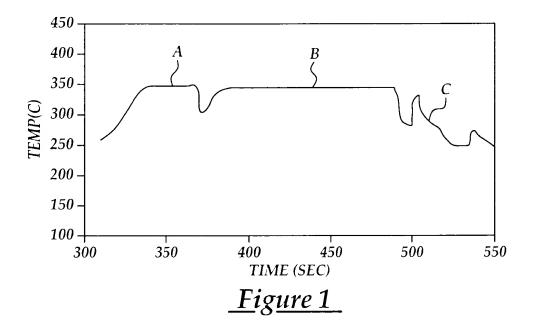
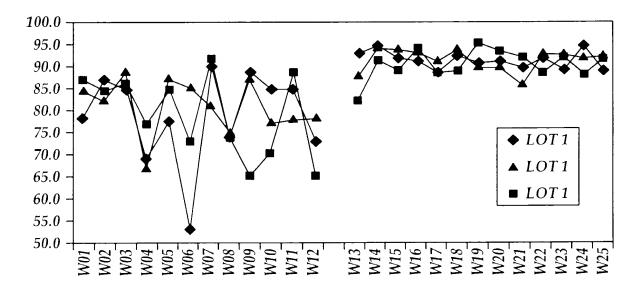
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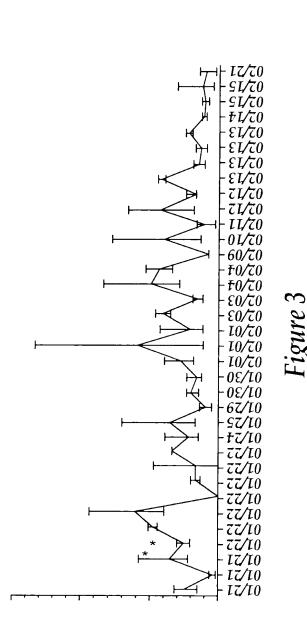




<u>Figure 2</u>

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			1		
STD (5 SEC)	HEAT UP 60 SEC STD (5 SEC)		HEAT UP 60 SEC STD (5 SEC)	STD (5 SEC)	HEAT UP 60 SEC
79.08	89'16	79.30	90.64	81.39	91.88
10.46	1.92	9.28	3.33	6.33	2.51
90.31	95.03	91.88	95.29	89.01	94.50
53.40	10.68	65.45	82.72	67.28	86.39